

OPA8780HP

High Speed

Infrared LED Chip

GaAlAs/GaAlAs

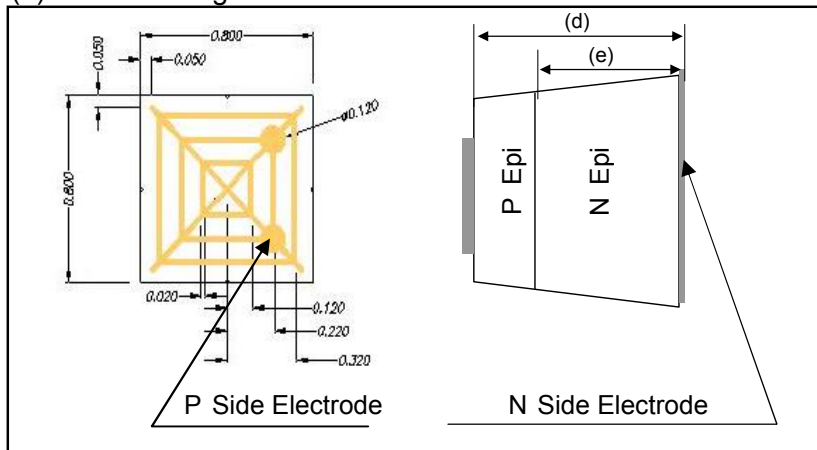
- 1. **Material** Substrate GaAlAs (N Type) Removed
 Epitaxial Layer GaAlAs (P/N Type)
- 2. **Electrode** N(Cathode) Side Gold Alloy
 P(Anode) Side Gold Alloy

3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_{F(1)}$		1.35	1.5	V	IF=10mA
	$V_{F(2)}$		1.5	1.7	V	IF=250mA
Reverse Voltage	V_R	5			V	IR=10uA
Power	P_O	2.0	3.0		mW	IF=20mA
Wavelength	λ_P		870		nm	IF=50mA
	$\Delta\lambda$		45		nm	IF=50mA
Rise Time	T_r		15		ns	
Fall Time	T_f		6.3		ns	

※ Note : LED chip is mounted on TO-18 gold header without resin coating.

- 4. **Mechanical Data** (a) Emission Area ----- 30.5mil x 30.5mil
- (b) Bottom Area ----- 31.5mil x 31.5mil
- (c) Bonding Pad ----- 120um
- (d) Chip Thickness ----- 7mil
- (e) Junction Height ----- 6.4mil



AUK Corp.

Eoyang factory, 513-5 Eoyang-dong, Iksan, 570-210, Korea

Tel. +82 63 839 1111 Fax. +82 63 835 8259

www.auk.co.kr

